



Low-Voltage Single SPDT Analog Switch

FEATURES

- Low Voltage Operation (1.8 V to 5.5 V)
- Low On-Resistance - $r_{DS(on)}$: 7 Ω
- Fast Switching - t_{ON} : 8 ns, t_{OFF} : 6 ns
- Low Charge Injection - Q_{INJ} : 5 pC
- Low Power Consumption
- TTL/CMOS Compatible
- 6-Pin SC-70 Package

BENEFITS

- Reduced Power Consumption
- Simple Logic Interface
- High Accuracy
- Reduce Board Space

APPLICATIONS

- Cellular Phones
- Communication Systems
- Portable Test Equipment
- Battery Operated Systems
- Sample and Hold Circuits

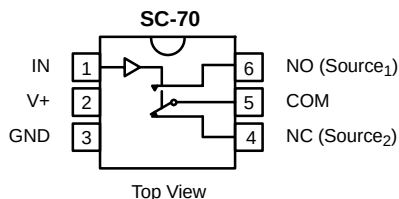
DESCRIPTION

The DG2002 is a single-pole/double-throw monolithic CMOS analog switch designed for high performance switching of analog signals. Combining low power, high speed (t_{ON} : 8 ns, t_{OFF} : 6 ns), low on-resistance ($r_{DS(on)}$: 7 Ω) and small physical size (SC70), the DG2002 is ideal for portable and battery powered applications requiring high performance and efficient use of board space.

The DG2002 is built on Vishay Siliconix's low voltage J12 process. An epitaxial layer prevents latchup. Break-before-make is guaranteed for DG2002.

Each switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



Device Marking: E2xx

TRUTH TABLE

Logic	NC	NO
0	ON	OFF
1	OFF	ON

ORDERING INFORMATION

Temp Range	Package	Part Number
-40 to 85°C	SC70-6	DG2002DL



ABSOLUTE MAXIMUM RATINGS

Reference to GND

V+	 -0.3 to +6 V
IN, COM, NC, NO ^a	 -0.3 to (V+ + 0.3 V)
Continuous Current (Any terminal)	 ± 50 mA
Peak Current	 ± 200 mA
(Pulsed at 1 ms, 10% duty cycle)	
Storage Temperature (D Suffix)	 -65 to 125°C

Power Dissipation (Packages)^b

6-Pin SO70 ^c	 250 mW
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Notes:

- Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- All leads welded or soldered to PC Board.
- Derate 6.5 mW/°C above 25°C

SPECIFICATIONS (V+ = 2.0 V)							
Parameter	Symbol	Test Conditions Otherwise Unless Specified V+ = 2.0 V, ±10%, VIN = 0.4 or 1.6 V ^e	Temp ^a	Limits −40 to 85°C			Unit
				Min ^b	Typ ^c	Max ^b	
Analog Switch							
Analog Signal Range ^d	VNO, VNC, VCOM		Full	0		V+	V
On-Resistance	rON	V+ = 1.8 V, VCOM = 1.0 V, INO, INC = 10 mA	Room Full ^d		38 39.3	46.1 47.1	Ω
rON Flatness ^d	rON Flatness	V+ = 1.8 V, VCOM = 0 to V+, INO, INC = 10 mA	Room		21		
Switch Off Leakage Current ^f	INO(off), INC(off)	V+ = 2.2 V VNO, VNC = 0.5 V/1.5 V, VCOM = 1.5 V/0.5 V	Room Full ^d	−250 −3.0		250 3.0	pA nA
	ICOM(off)		Room Full ^d	−250 −3.0		250 3.0	pA nA
Channel-On Leakage Current ^f	ICOM(on)	V+ = 2.2 V, VNO, VNC = VCOM = 0.5 V/1.5 V	Room Full ^d	−250 −3.0		250 3.0	pA nA
Digital Control							
Input High Voltage	VINH		Full	1.6			V
Input Low Voltage	VINL		Full			0.4	
Input Capacitance ^d	Cin		Full		3		pF
Input Current	IINL or IINH	VIN = 0 or V+	Full	−1		1	μA
Dynamic Characteristics							
Turn-On Time	tON	VNO or VNC = 1.5 V, RL = 300 Ω, CL = 35 pF Figures 1 and 2	Room Full ^d		22	31 32	ns
Turn-Off Time	tOFF		Room Full ^d		10	17 18	
Break-Before-Make Time	td		Room	1	12		
Charge Injection ^d	QINJ	CL = 1 nF, VGEN = 0 V, RGEN = 0 Ω, Figure 3	Room		5	10	pC
Off-Isolation ^d	OIRR	RL = 50 Ω, CL = 5 pF, f = 1 MHz	Room		−67		dB
Crosstalk ^d	XTALK		Room		−71		
NO, NC Off Capacitance ^d	CNO(off), CNC(off)	VIN = 0 or V+, f = 1 MHz	Room		5		pF
Channel-On Capacitance ^d	CON		Room		29		
Power Supply							
Power Supply Range	V+			1.8		2.2	V
Power Supply Current ^d	I+	VIN = 0 or V+			0.01	1.0	μA
Power Consumption	PC						2.2



SPECIFICATIONS (V+ = 3.0 V)							
Parameter	Symbol	Test Conditions Otherwise Unless Specified V+ = 3 V, ± 10%, VIN = 0.4 or 2.0 V ^e	Temp ^a	Limits −40 to 85°C			Unit
				Min ^b	Typ ^c	Max ^b	
Analog Switch							
Analog Signal Range ^d	VNO, VNC, VCOM		Full	0		V+	V
On-Resistance ^d	rON	V+ = 2.7 V, VCOM = 1.5 V, INO, INC = 10 mA	Room Full		12.2 13	14.8 15.8	Ω
rON Flatness ^d	rON Flatness	V+ = 2.7 V, VCOM = 0 to V+, INO, INC = 10 mA	Room		5		
Switch Off Leakage Current ^f	INO(off), INC(off)	V+ = 3.3 V VNO, VNC = 1 V/3 V, VCOM = 3 V/1 V	Room Full	−500 −4.0		500 4.0	pA nA
	ICOM(off)		Room Full	−500 −4.0		500 4.0	pA nA
Channel-On Leakage Current ^f	ICOM(on)	V+ = 3.3 V, VNO, VNC = VCOM = 1 V/3 V	Room Full	−500 −4.0		500 4.0	pA nA
Digital Control							
Input High Voltage	VINH		Full	2			V
Input Low Voltage	VINL		Full			0.4	
Input Capacitance ^d	Cin		Full		3		pF
Input Current	IINL or IINH	VIN = 0 or V+	Full	−1		1	μA
Dynamic Characteristics							
Turn-On Time ^d	tON	VNO or VNC = 2.0 V, RL = 300 Ω, CL = 35 pF Figure 1 and 2	Room Full		12	21 22	ns
Turn-Off Time ^d	tOFF		Room Full		7	14 15	
Break-Before-Make Time ^d	td		Room	1	6		
Charge Injection ^d	QINJ	CL = 1 nF, VGEN = 0 V, RGEN = 0 Ω, Figure 3	Room		5	10	pC
Off-Isolation ^d	OIRR	RL = 50 Ω, CL = 5 pF, f = 1 MHz	Room		−67		dB
Crosstalk ^d	XTALK		Room		−69		
NO, NC Off Capacitance ^d	CNO(off), CNC(off)	VIN = 0 or V+, f = 1 MHz	Room		5		pF
Channel-On Capacitance ^d	CON		Room		29		
Power Supply							
Power Supply Range	V+			2.7		3.3	V
Power Supply Current	I+	VIN = 0 or V+			0.01	1.0	μA
Power Consumption	PC					3.3	μW

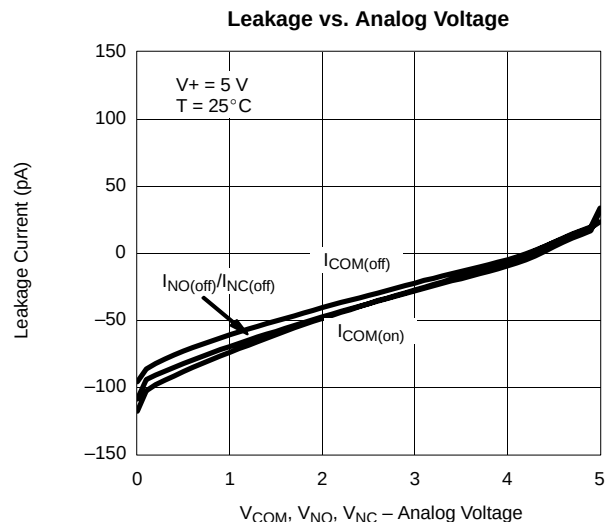
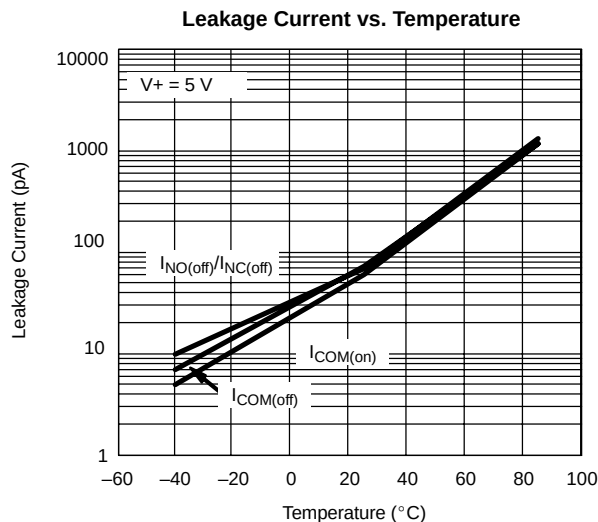
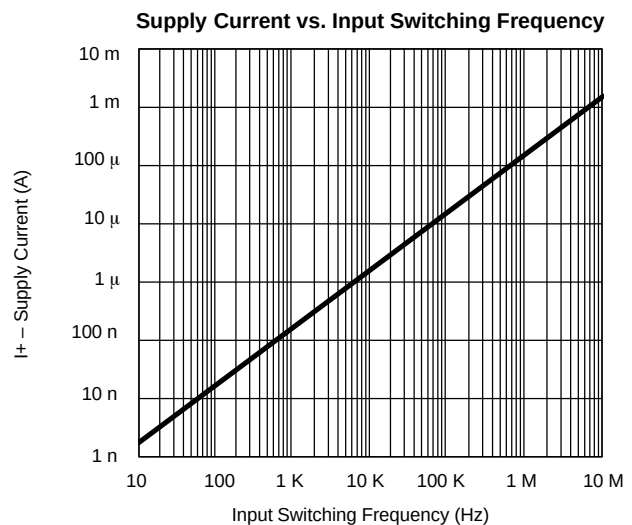
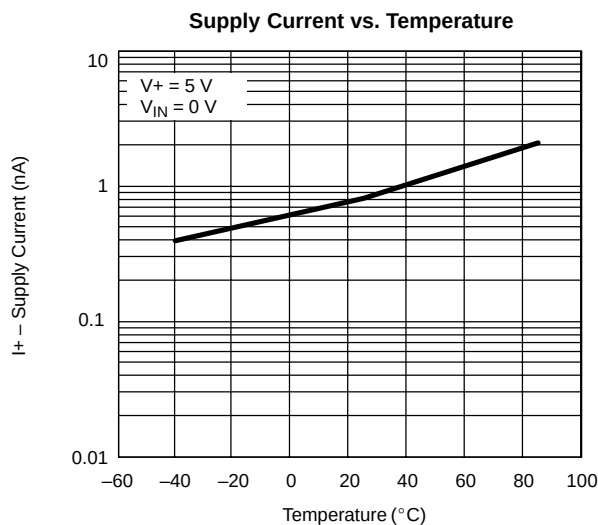
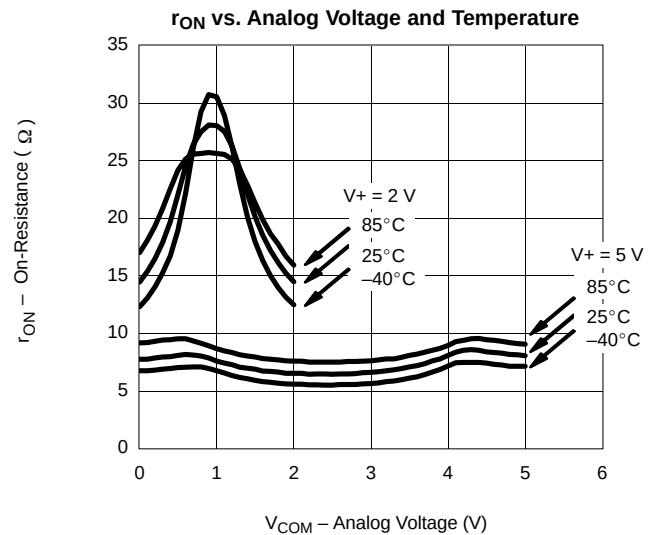
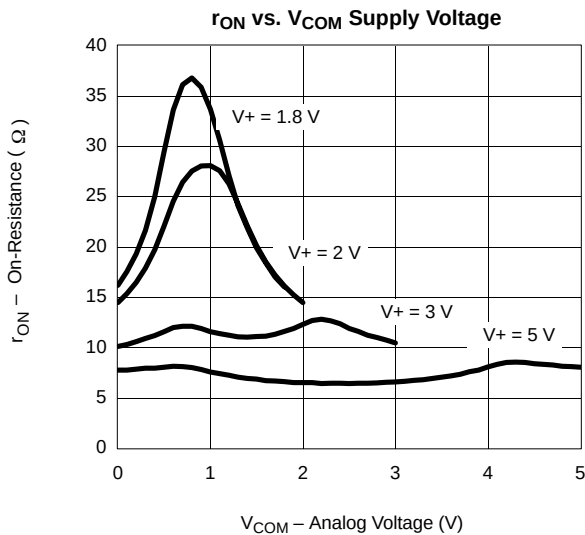


SPECIFICATIONS (V+ = 5.0 V)							
Parameter	Symbol	Test Conditions Otherwise Unless Specified V+ = 5 V, ±10%, VIN = 0.8 or 2.4 V ^e	Temp ^a	Limits –40 to 85°C			Unit
				Min ^b	Typ ^c	Max ^b	
Analog Switch							
Analog Signal Range ^d	VNO, VNC, VCOM		Full	0		V+	V
On-Resistance	rON	V+ = 4.5 V, VCOM = 3 V, INO, INC = 10 mA	Room Full		6.4 7.4	7.8 8.8	Ω
rON Flatness ^d	rON Flatness	V+ = 4.5 V, VCOM = 0 to V+, INO, INC = 10 mA	Room		3		
Switch Off Leakage Current	INO(off), INC(off)	V+ = 5.5 V VNO, VNC = 1 V/4.5 V, VCOM = 4.5 V/1 V	Room Full	–1.0 –4.0		1.0 4.0	nA
	ICOM(off)		Room Full	–1.0 –4.0		1.0 4.0	
Channel-On Leakage Current	ICOM(on)	V+ = 5.5 V, V+ = 5.5 V VNO, VNC = VCOM = 1 V/4.5 V	Room Full	–1.0 –4.5		1.0 4.5	
Digital Control							
Input High Voltage	VINH		Full	2.4			V
Input Low Voltage	VINL		Full			0.8	
Input Capacitance	Cin		Full		3		pF
Input Current	IINL or IINH	VIN = 0 or V+	Full	–1		1	μA
Dynamic Characteristics							
Turn-On Time ^d	tON	VNO or VNC = 3 V, RL = 300 Ω, CL = 35 pF Figure 1 and 2	Room Full		8	15 16	ns
Turn-Off Time ^d	tOFF		Room Full		6	13 14	
Break-Before-Make Time ^d	td		Room	1	4		
Charge Injection ^d	QINJ	CL = 1 nF, VGEN = 0 V, RGEN = 0 Ω, Figure 3	Room		5	10	pC
Off-Isolation ^d	OIRR	RL = 50 Ω, CL = 5 pF, f = 1 MHz	Room		–69		dB
Crosstalk ^d	XTALK		Room		–69		
Source-Off Capacitance ^d	CNO(off), CNC(off)	VIN = 0 or V+, f = 1 MHz	Room		5		pF
Channel-On Capacitance ^d	CON		Room		29		
Power Supply							
Power Supply Range	V+			4.5		5.5	V
Power Supply Current	I+	VIN = 0 or V+			0.01	1.0	μA
Power Consumption	PC						5.5

Notes:

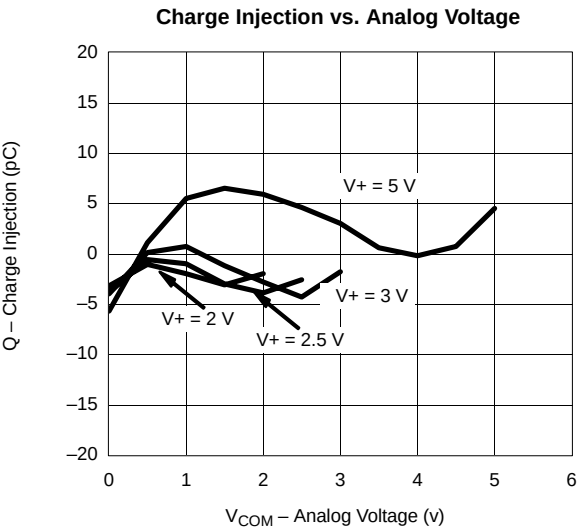
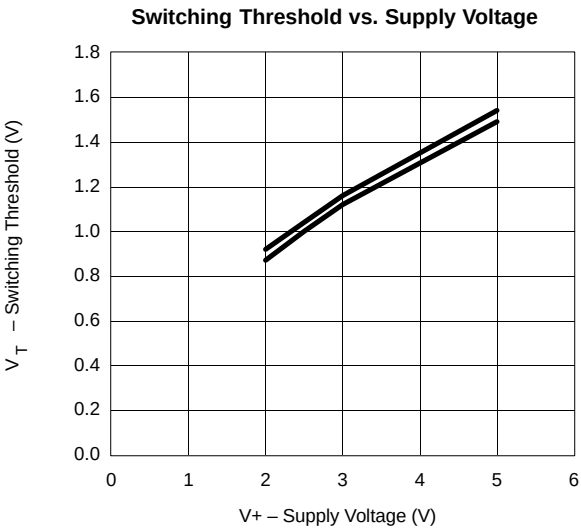
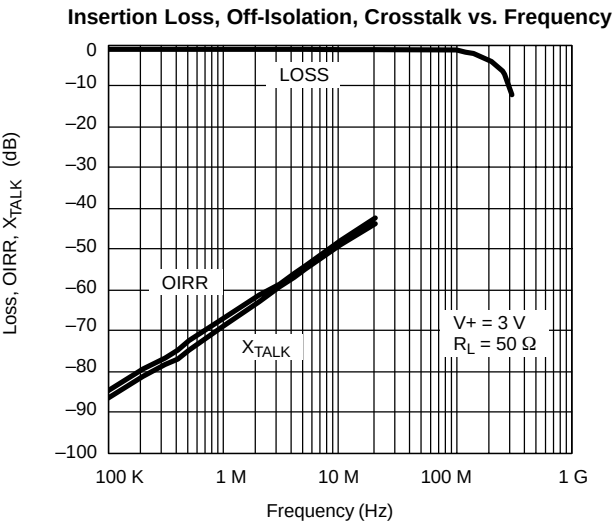
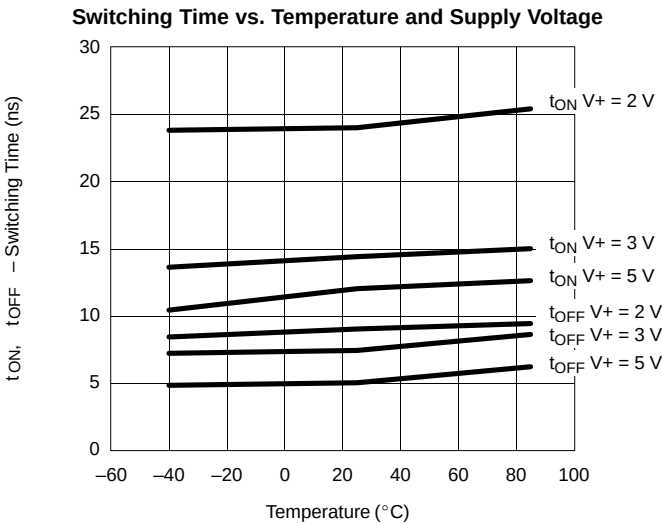
- Room = 25°C, Full = as determined by the operating suffix.
- The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- Typical values are for design aid only, not guaranteed nor subject to production testing.
- Guarantee by design, nor subjected to production test.
- V_{IN} = input voltage to perform proper function.
- Guaranteed by 5-V leakage testing, not production tested.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

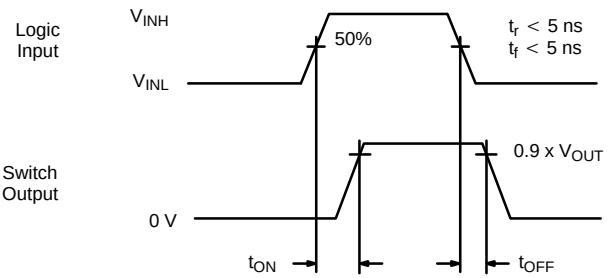
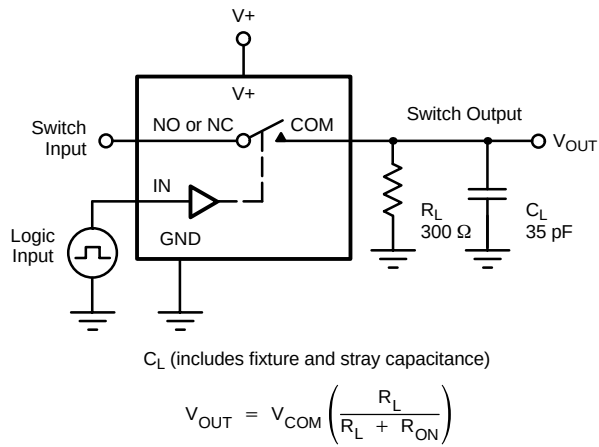




TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



TEST CIRCUITS



Logic "1" = Switch On
Logic input waveforms inverted for switches that have the opposite logic sense.

FIGURE 1. Switching Time

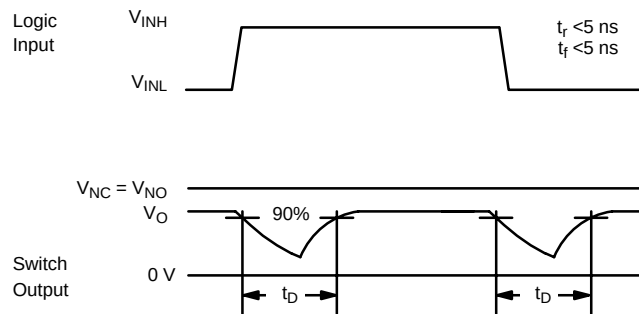
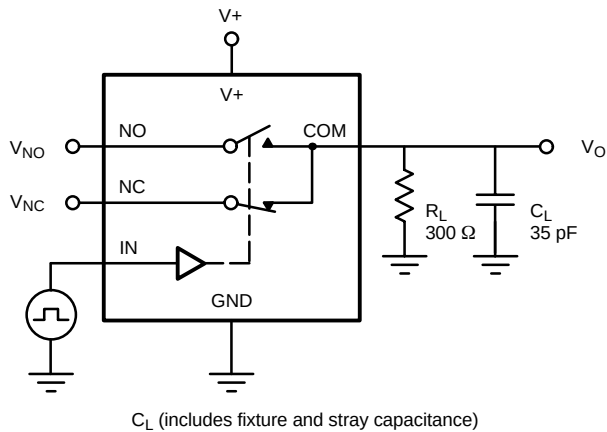
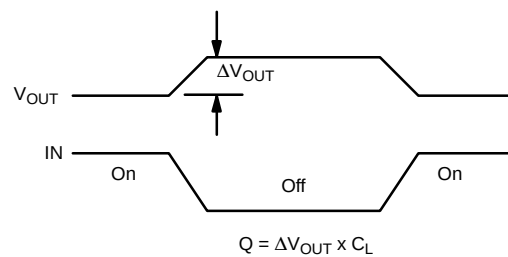
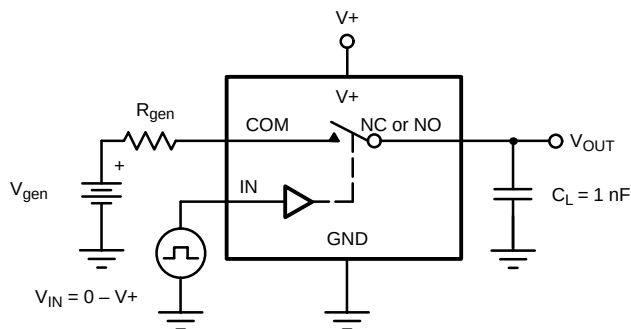


FIGURE 2. Break-Before-Make Interval



IN depends on switch configuration: input polarity determined by sense of switch.

FIGURE 3. Charge Injection



TEST CIRCUITS

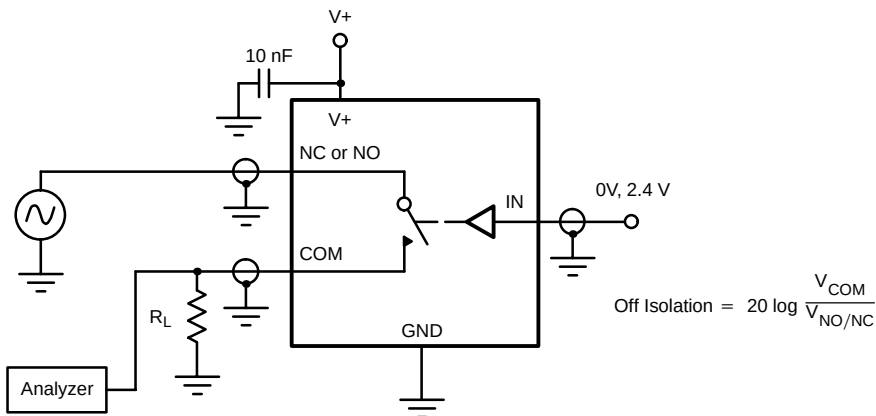


FIGURE 4. Off-Isolation

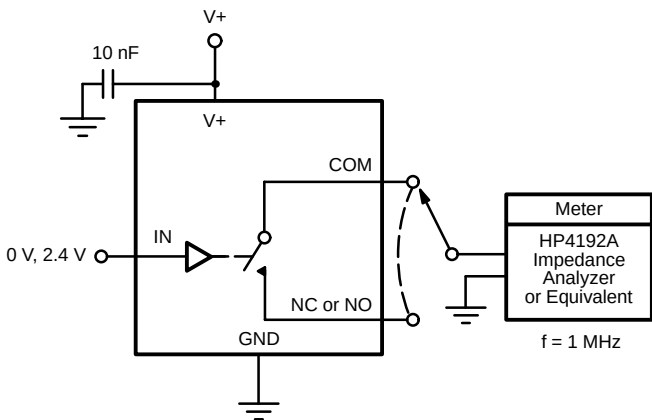


FIGURE 5. Channel Off/On Capacitance